

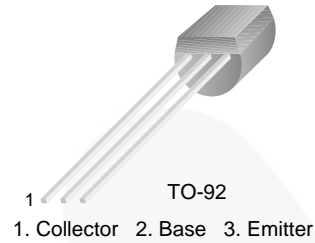


October 2014

BC337 / BC338 NPN Epitaxial Silicon Transistor

Features

- Switching and Amplifier Applications
- Suitable for AF-Driver Stages and Low-Power Output Stages
- Complement to BC327 / BC328



Ordering Information

Part Number	Top Mark	Package	Packing Method
BC33716BU	BC33716	TO-92 3L	Bulk
BC33716TA	BC33716	TO-92 3L	Ammo
BC33716TFR	BC33716	TO-92 3L	Tape and Reel
BC33725BU	BC33725	TO-92 3L	Bulk
BC33725TA	BC33725	TO-92 3L	Ammo
BC33725TAR	BC33725	TO-92 3L	Ammo
BC33725TF	BC33725	TO-92 3L	Tape and Reel
BC33725TFR	BC33725	TO-92 3L	Tape and Reel
BC33740BU	BC33740	TO-92 3L	Bulk
BC33740TA	BC33740	TO-92 3L	Ammo
BC33825TA	BC33825	TO-92 3L	Ammo

Absolute Maximum Ratings

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only. Values are at $T_A = 25^\circ\text{C}$ unless otherwise noted.

Symbol	Parameter	Value	Unit	
V_{CES}	Collector-Emitter Voltage	BC337	50	V
		BC338	30	
V_{CEO}	Collector-Emitter Voltage	BC337	45	V
		BC338	25	
V_{EBO}	Emitter-Base Voltage	5	V	
I_C	Collector Current (DC)	800	mA	
T_J	Junction Temperature	150	$^\circ\text{C}$	
T_{STG}	Storage Temperature	-55 to 150	$^\circ\text{C}$	

BC337 / BC338 — NPN Epitaxial Silicon Transistor

Thermal Characteristics⁽¹⁾Values are at $T_A = 25^\circ\text{C}$ unless otherwise noted.

Symbol	Parameter	Value	Unit
P_D	Power Dissipation	625	mW
	Derate Above 25°C	5.0	mW/ $^\circ\text{C}$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	200	$^\circ\text{C}/\text{W}$

Note:

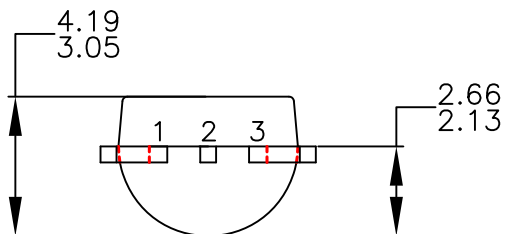
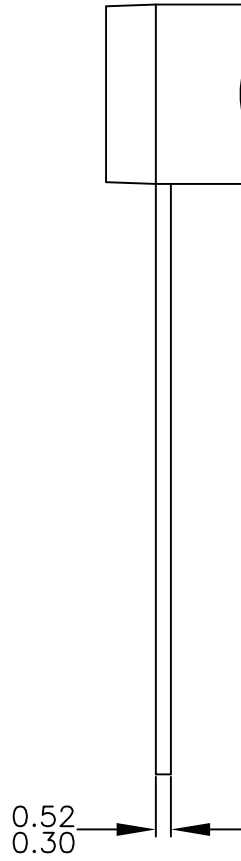
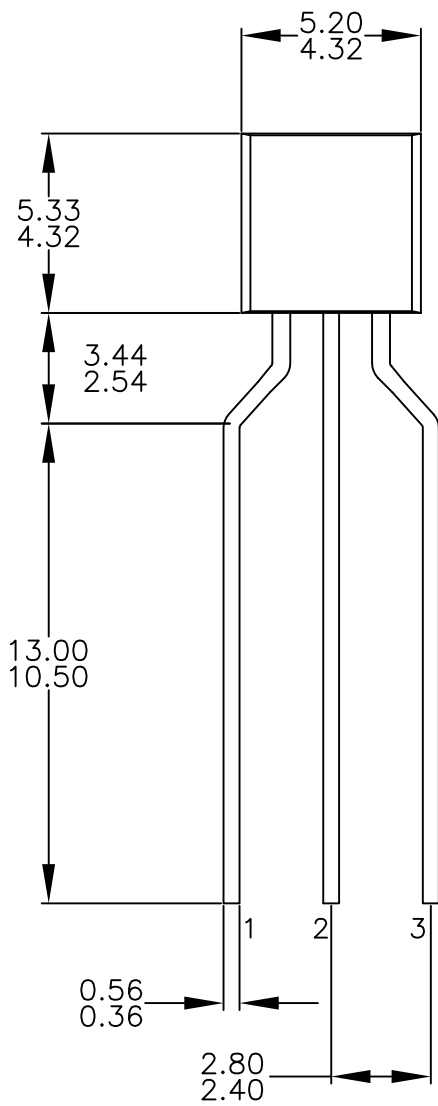
1. PCB size: FR-4, 76 mm x 114 mm x 1.57 mm (3.0 inch x 4.5 inch x 0.062 inch) with minimum land pattern size.

Electrical CharacteristicsValues are at $T_A = 25^\circ\text{C}$ unless otherwise noted.

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit	
BV_{CEO}	Collector-Emitter Breakdown Voltage	BC337	$I_C = 10\text{ mA}, I_B = 0$	45		V	
		BC338		25			
BV_{CES}	Collector-Emitter Breakdown Voltage	BC337	$I_C = 0.1\text{ mA}, V_{BE} = 0$	50		V	
		BC338		30			
BV_{EBO}	Emitter-Base Breakdown Voltage	$I_E = 0.1\text{ mA}, I_C = 0$	5			V	
I_{CES}	Collector Cut-Off Current	BC337	$V_{CE} = 45\text{ V}, I_B = 0$		2	100	nA
		BC338	$V_{CE} = 25\text{ V}, I_B = 0$		2	100	
h_{FE1}	DC Current Gain		$V_{CE} = 1\text{ V}, I_C = 100\text{ mA}$	100		630	
h_{FE2}			$V_{CE} = 1\text{ V}, I_C = 300\text{ mA}$	60			
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = 500\text{ mA}, I_B = 50\text{ mA}$			0.7	V	
$V_{BE(on)}$	Base-Emitter On Voltage	$V_{CE} = 1\text{ V}, I_C = 300\text{ mA}$			1.2	V	
f_T	Current Gain Bandwidth Product	$V_{CE} = 5\text{ V}, I_C = 10\text{ mA}, f = 50\text{ MHz}$		100		MHz	
C_{ob}	Output Capacitance	$V_{CB} = 10\text{ V}, I_E = 0, f = 1\text{ MHz}$		12		pF	

 h_{FE} Classification

Classification	16	25	40
h_{FE1}	100 ~ 250	160 ~ 400	250 ~ 630
h_{FE2}	60 ~	100 ~	170 ~



NOTES: UNLESS OTHERWISE SPECIFIED

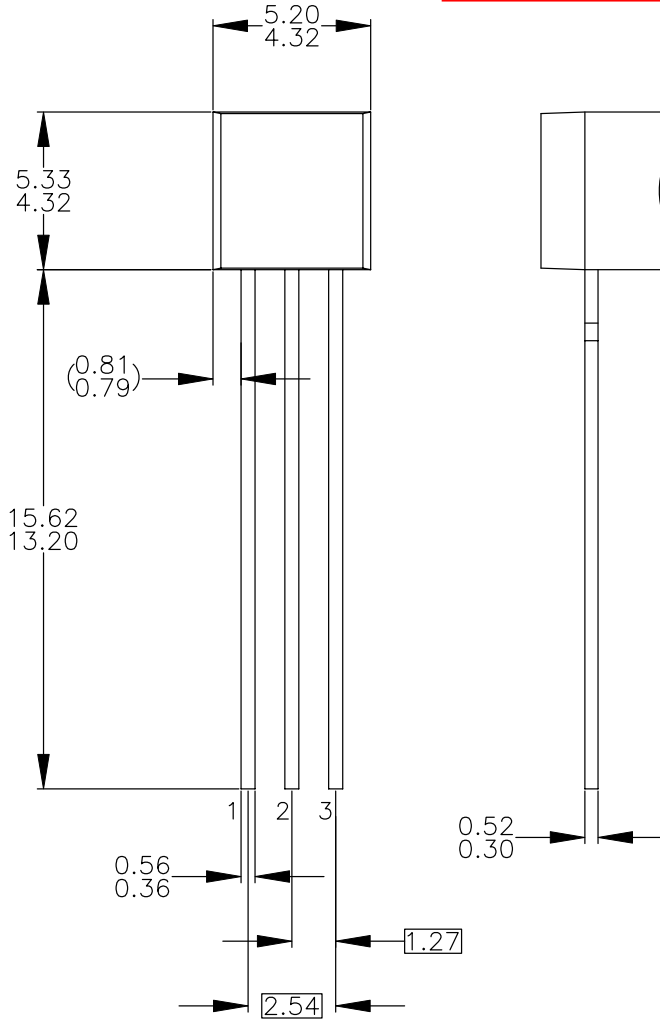
- A. DRAWING CONFORMS TO JEDEC MS-013, VARIATION AC.
- B. ALL DIMENSIONS ARE IN MILLIMETERS.
- C. DRAWING CONFORMS TO ASME Y14.5M-2009.
- D. DRAWING FILENAME: MKT-ZA03FREV3.
- E. FAIRCHILD SEMICONDUCTOR.

THIS DRAWING IS THE PROPERTY OF FAIRCHILD SEMICONDUCTOR CORPORATION. NO USE THEREOF SHALL BE MADE OTHER THAN AS A REFERENCE FOR PROPOSALS AS SUBMITTED TO FAIRCHILD SEMICONDUCTOR CORPORATION FOR JOBS TO BE EXECUTED IN CONFORMANCE WITH SUCH PROPOSALS UNLESS THE CONSENT OF SAID FAIRCHILD SEMICONDUCTOR CORPORATION HAS PREVIOUSLY BEEN OBTAINED. NO PART OF THIS DRAWING SHALL BE COPIED OR DUPLICATED OR ITS CONTENTS DISCLOSED. THE INFORMATION CONTAINED ON THIS DRAWING IS CONFIDENTIAL AND PROPRIETARY.

APPROVED
 July-14-2008

REVISIONS

NO.	DESCRIPTION	DATE	NAME/SITE
A	RELEASE TO DOCUMENT CONTROL	MAR.4'96	RP
B	RDRW AS PER STD DWG TEMPLATE. CHG DIM REF FR DUAL DIM INCH(MM) TO SINGLE DIM MM. CHG LD PITCH DIM FR 1.14-1.40 TO 1.27 BSC. ADD DIM 2.54 BSC. CHG PKG WIDTH DIM FR 4.32- 4.70 TO 4.32-4.83; CHG PKG HEIGHT DIM FR 4.32-4.70 TO 4.32-4.78; CHG LD THICK DIM FR 0.30- 0.48 TO 0.30-0.52; DAMBAR-PKG DIM FR 1.27-1.65 TO 0.90-1.65; LD LGH DIM FR 14.47-15.64 TO 14.47-15.62; PKG DIM: 1.02-1.52 TO 0.92-1.52, 3.81-4.45 TO 3.40-4.80; NOTE 2: ADD DMOS "M" OPT'N AND LEGEND; NOTE B PKG 94 JFET OPT'N: CHG D TO S, CHG S TO D. ADD NOTE C. MOVE NOTE B INFO FR PKG 97&98 TO NEW NOTE D.	4OCT1999	RCM/MRG
3	CHG LD LEN FR 1.81 TO 1.88 ; CHG MOLD BODY HT FR 1.33 TO 1.33 ; CHG PKG EDGE TO LD EDGE DIST FR (0.81) TO (0.81); CHG MOLD BODY WIDTH FR 1.33 TO 1.33 ; ADD PKG THICKNESS DIM "E"; CHG "S" DIM FR 2.13 TO 2.13 ; REMOVE DAMBAR & EJECTOR PIN LOCATOR FEATURES & DIMENSIONS; REMOVE MOLDED SURFACE & DRAFT ANGLE DIMS; ADD NOTE ON JEDEC REFERENCE; ADD NOTE ON ASME Y14.5M-1994; REMOVE NOTE ON L34Z OPTION; ADD NOTE ON DWG FILENAME.	12FEB08	BMR/FSCP



- NOTES: UNLESS OTHERWISE SPECIFIED
- A) DRAWING WITH REFERENCE TO JEDEC TO-92 RECOMMENDATIONS.
 - B) ALL DIMENSIONS ARE IN MILLIMETERS.
 - C) DRAWING CONFORMS TO ASME Y14.5M-1994.
 - D) TO-92 (92,94,96,97,98) PIN CONFIGURATION:

PIN	92			94			96			97			98		
	P	F	M	P	F	M	B	F	M	P	F	M	P	F	M
1	E	S	S	E	S	S	B	D	G	C	G	D	C	G	D
2	B	D	G	C	G	D	E	S	S	B	D	G	E	S	S
3	C	G	D	B	D	G	C	G	D	E	S	S	B	D	G

LEGEND:

P - BIPOLAR	E - EMITTER	D - DRAIN
F - JFET	B - BASE	S - SOURCE
M - DMOS	C - COLLECTOR	G - GATE






- E) FOR PACKAGE 92, 94, 96, 97 AND 98: PIN CONFIGURATION DRAIN "D" AND SOURCE "S" ARE INTERCHANGEABLE AT JFET "F" OPTION.
- F) DRAWING FILENAME: MKT-ZA03DREV3.

APPROVALS	DATE	 FAIRCHILD SEMICONDUCTOR™
DRAWN: J.U. COMPARATIVO JR.	03APR2008	
CHECKED: L. GALERA		
APPROVED: M.R. GESTOLE		
G.S. BAJE		3LD, TO-92, MOLDED STD STRAIGHT LD (NO EOL CODE)
		SCALE: 1:1 SIZE: N/A DRAWING NUMBER: MKT-ZA03D FORMERLY: N/A
		REV: 3 SHEET: 1 OF 1



TRADEMARKS

The following includes registered and unregistered trademarks and service marks, owned by Fairchild Semiconductor and/or its global subsidiaries, and is not intended to be an exhaustive list of all such trademarks.

- | | | | |
|---|--|---|---|
| AccuPower™ | F-PFS™ | OPTOPLANAR® |  |
| Awinda® | FRFET® |  | TinyBoost® |
| AX-CAP®* | Global Power Resource SM | PowerTrench® | TinyBuck® |
| BitSiC™ | GreenBridge™ | PowerXS™ | TinyCalc™ |
| Build it Now™ | Green FPS™ | Programmable Active Droop™ | TinyLogic® |
| CorePLUS™ | Green FPS™ e-Series™ | QFET® | TINYOPTO™ |
| CorePOWER™ | Gmax™ | QS™ | TinyPower™ |
| CROSSVOL™ | GTO™ | Quiet Series™ | TinyPWM™ |
| CTL™ | IntelliMAX™ | RapidConfigure™ | TinyWire™ |
| Current Transfer Logic™ | ISOPLANAR™ |  | TranSiC™ |
| DEUXPEED® | Making Small Speakers Sound Louder and Better™ | Saving our world, 1mW/W/kW at a time™ | TriFault Detect™ |
| Dual Cool™ | MegaBuck™ | SignalWise™ | TRUECURRENT®* |
| EcoSPARK® | MICROCOUPLER™ | SmartMax™ | μSerDes™ |
| EfficientMax™ | MicroFET™ | SMART START™ |  |
| ESBC™ | MicroPak™ | Solutions for Your Success™ | UHC® |
|  | MicroPak2™ | SPM® | Ultra FRFET™ |
| Fairchild® | MillerDrive™ | STEALTH™ | UniFET™ |
| Fairchild Semiconductor® | MotionMax™ | SuperFET® | VCX™ |
| FACT Quiet Series™ | MotionGrid® | SuperSOT™-3 | VisualMax™ |
| FACT® | MTi® | SuperSOT™-6 | VoltagePlus™ |
| FAST® | MTx® | SuperSOT™-8 | XS™ |
| FastvCore™ | MVN® | SupreMOS® | Xsens™ |
| FETBench™ | mWSaver® | SyncFET™ | 仙童™ |
| FPS™ | OptoHiT™ | Sync-Lock™ | |
| | OPTOLOGIC® | | |

* Trademarks of System General Corporation, used under license by Fairchild Semiconductor.

DISCLAIMER

FAIRCHILD SEMICONDUCTOR RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION, OR DESIGN. TO OBTAIN THE LATEST, MOST UP-TO-DATE DATASHEET AND PRODUCT INFORMATION, VISIT OUR WEBSITE AT [HTTP://WWW.FAIRCHILDSEMI.COM](http://www.fairchildsemi.com). FAIRCHILD DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS. THESE SPECIFICATIONS DO NOT EXPAND THE TERMS OF FAIRCHILD'S WORLDWIDE TERMS AND CONDITIONS, SPECIFICALLY THE WARRANTY THEREIN, WHICH COVERS THESE PRODUCTS.

LIFE SUPPORT POLICY

FAIRCHILD'S PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS WRITTEN APPROVAL OF FAIRCHILD SEMICONDUCTOR CORPORATION.

As used herein:

- Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body or (b) support or sustain life, and (c) whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in a significant injury of the user.
- A critical component in any component of a life support, device, or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

ANTI-COUNTERFEITING POLICY

Fairchild Semiconductor Corporation's Anti-Counterfeiting Policy. Fairchild's Anti-Counterfeiting Policy is also stated on our external website, www.fairchildsemi.com, under Sales Support.

Counterfeiting of semiconductor parts is a growing problem in the industry. All manufacturers of semiconductor products are experiencing counterfeiting of their parts. Customers who inadvertently purchase counterfeit parts experience many problems such as loss of brand reputation, substandard performance, failed applications, and increased cost of production and manufacturing delays. Fairchild is taking strong measures to protect ourselves and our customers from the proliferation of counterfeit parts. Fairchild strongly encourages customers to purchase Fairchild parts either directly from Fairchild or from Authorized Fairchild Distributors who are listed by country on our web page cited above. Products customers buy either from Fairchild directly or from Authorized Fairchild Distributors are genuine parts, have full traceability, meet Fairchild's quality standards for handling and storage and provide access to Fairchild's full range of up-to-date technical and product information. Fairchild and our Authorized Distributors will stand behind all warranties and will appropriately address any warranty issues that may arise. Fairchild will not provide any warranty coverage or other assistance for parts bought from Unauthorized Sources. Fairchild is committed to combat this global problem and encourage our customers to do their part in stopping this practice by buying direct or from authorized distributors.

PRODUCT STATUS DEFINITIONS

Definition of Terms

Datasheet Identification	Product Status	Definition
Advance Information	Formative / In Design	Datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary	First Production	Datasheet contains preliminary data; supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve design.
No Identification Needed	Full Production	Datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve the design.
Obsolete	Not In Production	Datasheet contains specifications on a product that is discontinued by Fairchild Semiconductor. The datasheet is for reference information only.

Rev. I72